

SANYO	No.1943A	2SA1392/2SC3383
		PNP/NPN Epitaxial Planar Silicon Transistors
AF Amp Applications		

Features

- . Adoption of FBET process
- . AF amp

(): 2SA1392

Absolute Maximum Ratings at Ta=25°C

			unit
Collector to Base Voltage	V_{CB0}	(-)60	V
Collector to Emitter Voltage	V_{CE0}	(-)50	V
Emitter to Base Voltage	V_{EB0}	(-)6	V
Collector Current	I_C	(-)200	mA
Collector Current (Pulse)	I_{CP}	(-)400	mA
Collector Dissipation	P_C	400	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

Electrical Characteristics at Ta=25°C

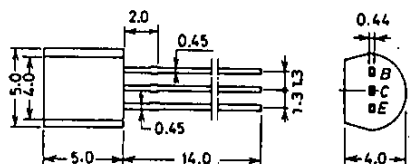
			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)40V, I_E=0$			(-)0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)5V, I_C=0$			(-)0.1	μA
DC Current Gain	$h_{FE}(1)$	$V_{CE}=(-)6V, I_C=(-)1mA$	100*		560*	
	$h_{FE}(2)$	$V_{CE}=(-)6V, I_C=(-)0.1mA$	70			
Gain-Bandwidth Product	f_T	$V_{CE}=(-)6V, I_C=(-)10mA$		250		MHz
				(200)		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)100mA, I_B=(-)10mA$			(-)0.3	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)100mA, I_B=(-)10mA$			(-)1.0	V
Output Capacitance	c_{ob}	$V_{CB}=(-)6V, f=1MHz$		2.7		pF
				(3.7)		pF
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu A, I_E=0$	(-)60			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1mA, R_{BE}=\infty$	(-)50			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu A, I_C=0$	(-)6			V

*: The 2SA1392/2SC3383 are classified by 1mA h_{FE} as follows:

100	R	200	140	S	280	200	T	400	280	U	560
-----	---	-----	-----	---	-----	-----	---	-----	-----	---	-----

Package Dimensions 2003A

(unit: mm)

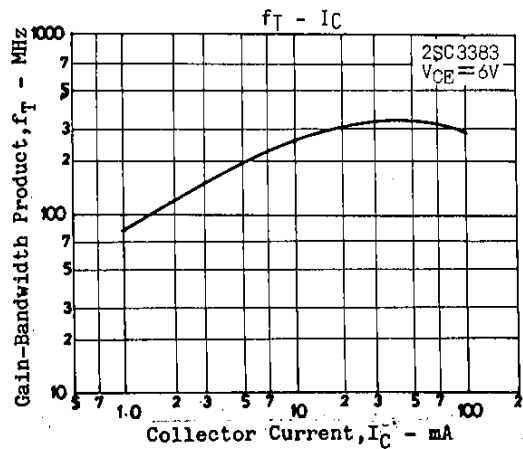
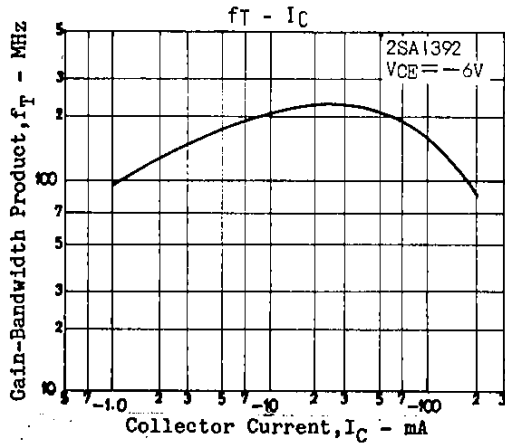
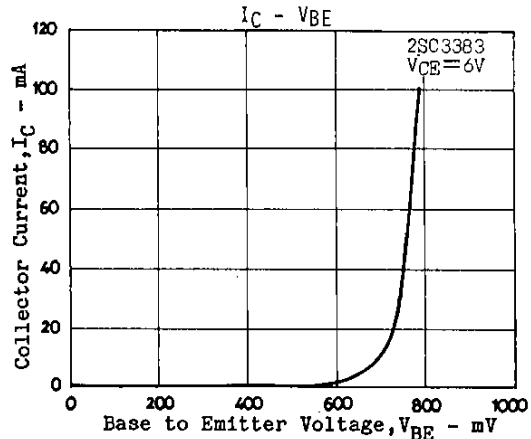
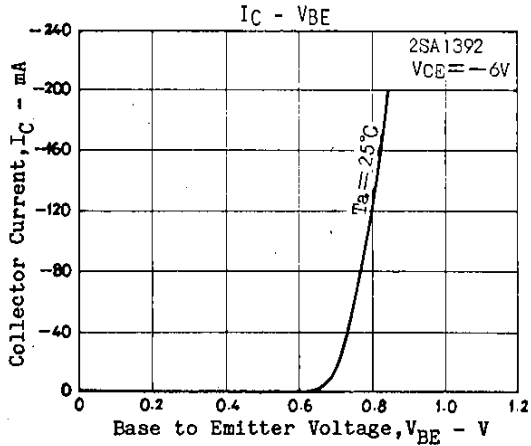
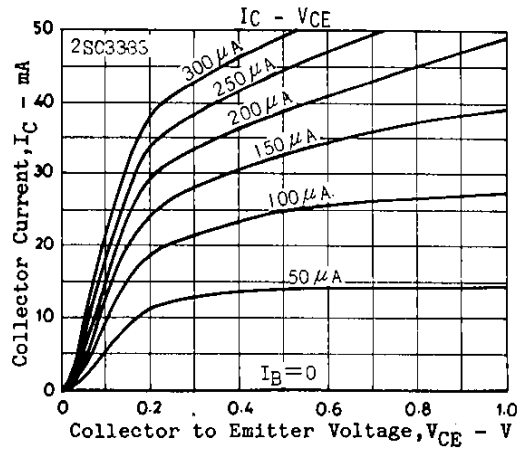
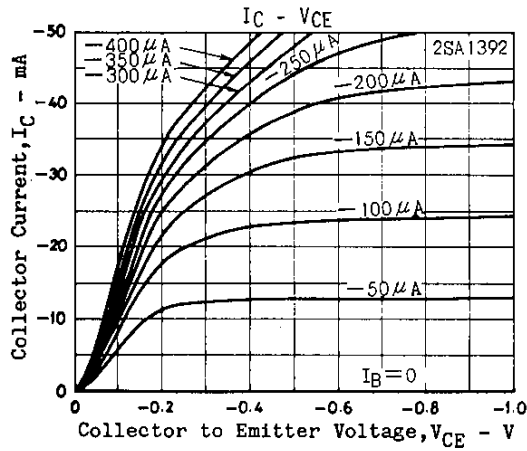
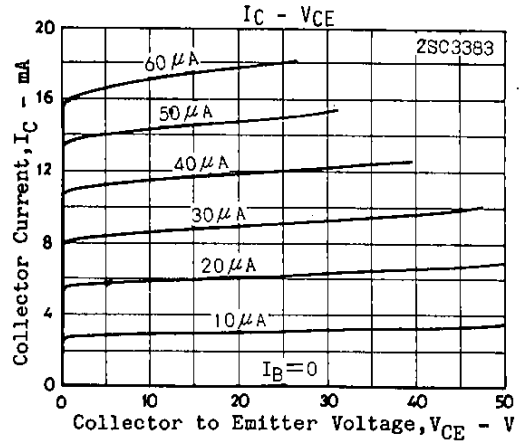
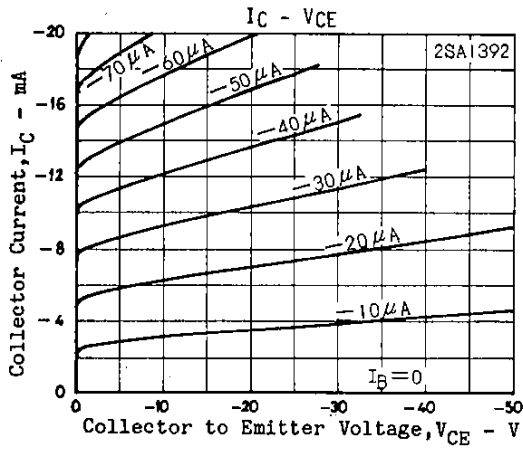


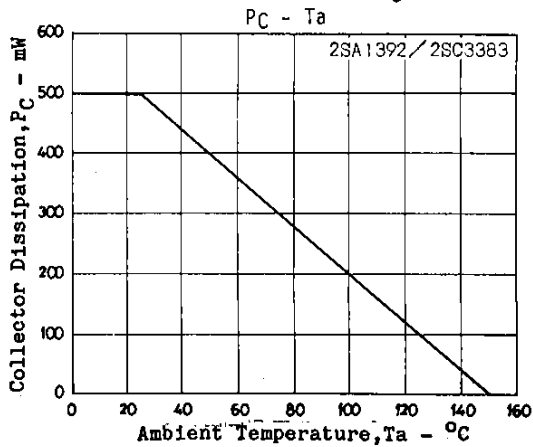
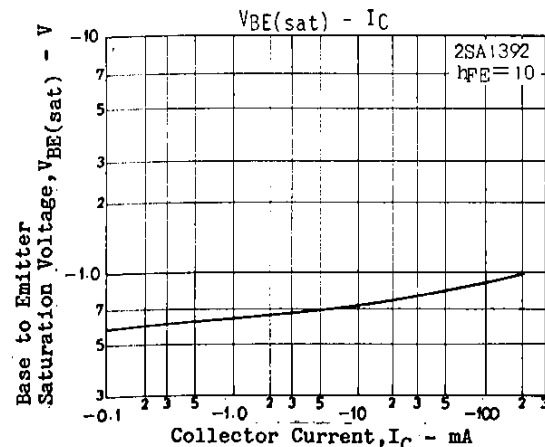
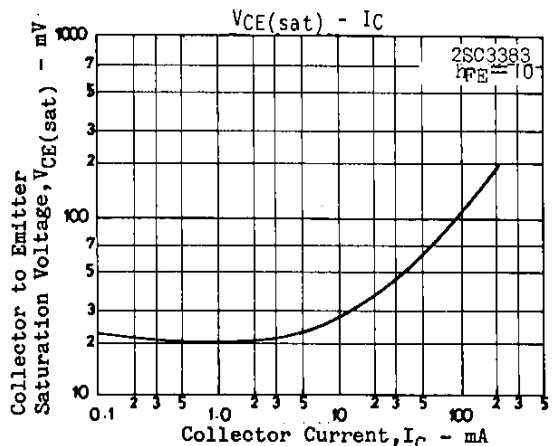
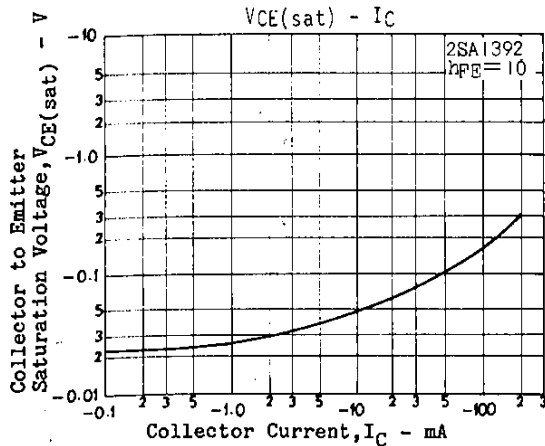
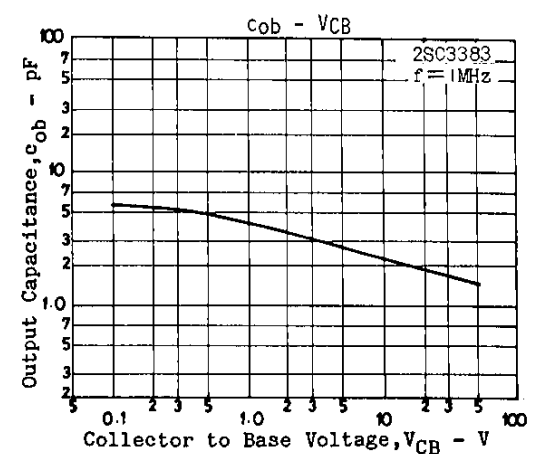
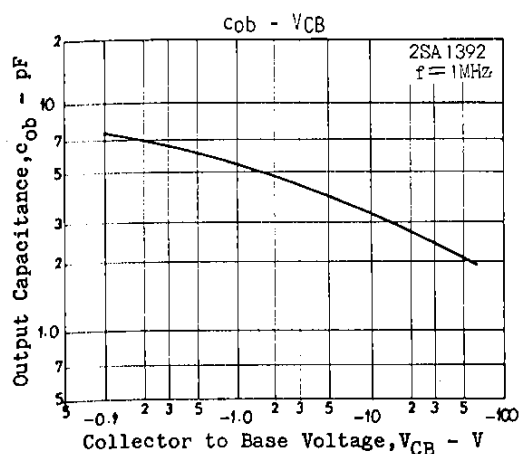
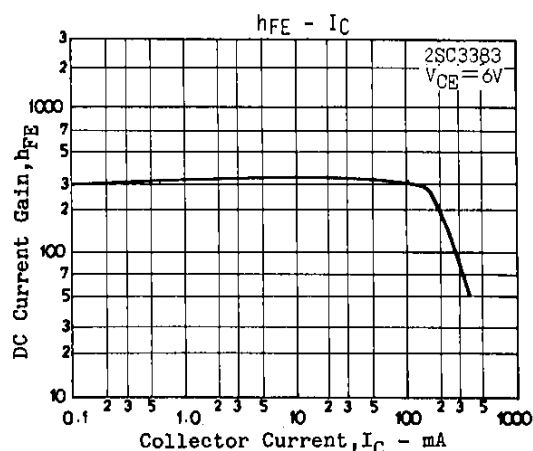
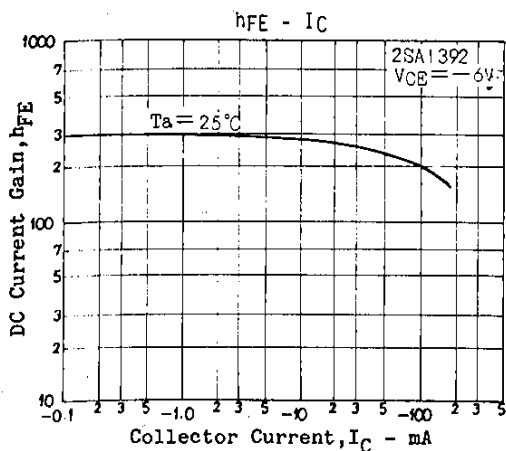
JEDEC: TO-92
EIAJ: SC-43
SANYO: NP

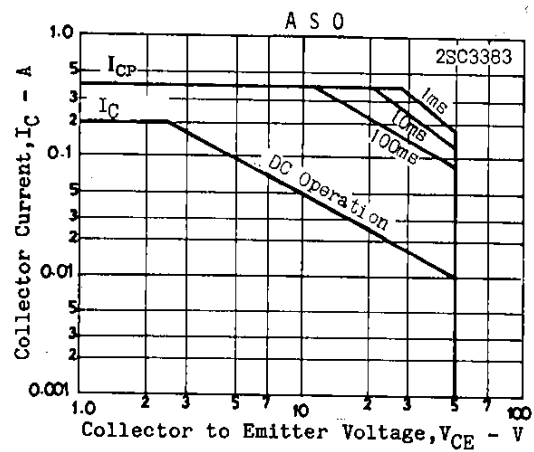
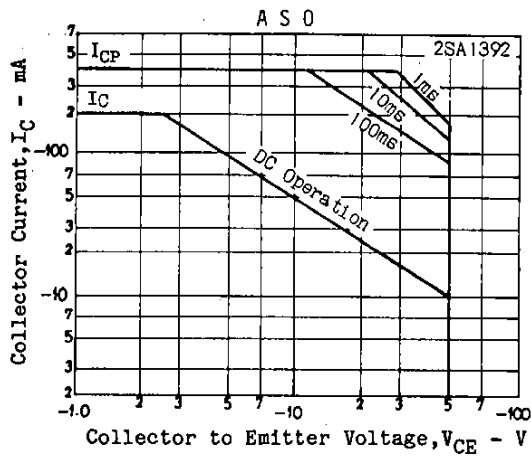
B. Base
C. Collector
E. Emitter

SANYO Electric Co., Ltd. Semiconductor Business Headquarters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

4277TA, TS No. 1943-1/4







- No products described or contained herein are intended for use in surgical implants, life-support systems, aerospace equipment, nuclear power control systems, vehicles, disaster/crime-prevention equipment and the like, the failure of which may directly or indirectly cause injury, death or property loss.
- Anyone purchasing any products described or contained herein for an above-mentioned use shall:
 - ① Accept full responsibility and indemnify and defend SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors and all their officers and employees, jointly and severally, against any and all claims and litigation and all damages, cost and expenses associated with such use:
 - ② Not impose any responsibility for any fault or negligence which may be cited in any such claim or litigation on SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors or any of their officers and employees jointly or severally.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. SANYO believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.